

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2N5732

DESCRIPTION

- With TO-3 package
- High current capability

APPLICATIONS

- For linear amplifier and inductive switching applications

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

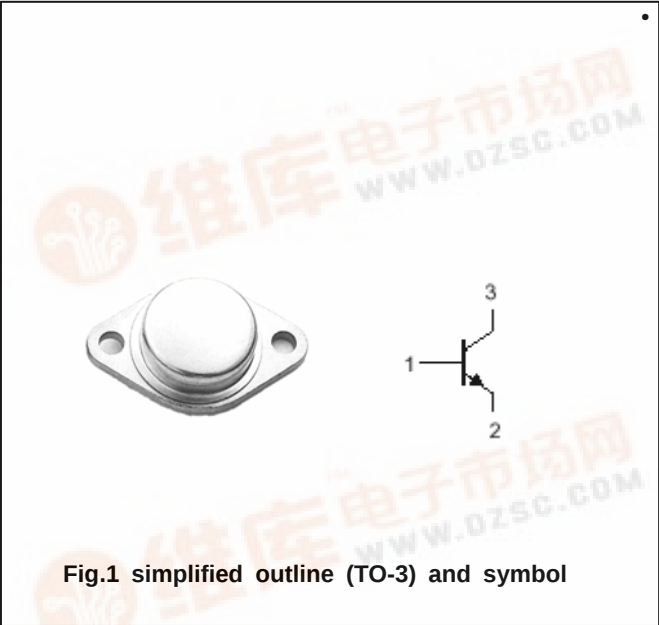


Fig.1 simplified outline (TO-3) and symbol

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	100	V
V _{CEO}	Collector-emitter voltage	Open base	80	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		20	A
I _{CM}	Collector current-peak		30	A
P _T	Total power dissipation	T _C =25℃	87.5	W
T _j	Junction temperature		150	℃
T _{stg}	Storage temperature		-65~200	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance junction to case	1.17	℃/W



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CHARACTERISTICS

 $T_j=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEQ(SUS)}$	Collector-emitter sustaining voltage	$I_C=0.2\text{A}; I_B=0$	80			V
$V_{CEsat-1}$	Collector-emitter saturation voltage	$I_C=10\text{A}; I_B=1\text{A}$			1.4	V
$V_{CEsat-2}$	Collector-emitter saturation voltage	$I_C=20\text{A}; I_B=4\text{A}$			4.0	V
V_{BE}	Base-emitter on voltage	$I_C=10\text{A}; V_{CE}=4\text{V}$			2.2	V
I_{CBO}	Collector cut-off current	$V_{CB}=100\text{V}; I_E=0$			0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=7\text{V}; I_C=0$			0.1	mA
h_{FE-1}	DC current gain	$I_C=5\text{A}; V_{CE}=2\text{V}$	30		300	
h_{FE-2}	DC current gain	$I_C=20\text{A}; V_{CE}=4\text{V}$	5			
f_T	Transition frequency	$I_C=1\text{A}; V_{CE}=10\text{V}$	30			MHz

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PACKAGE OUTLINE

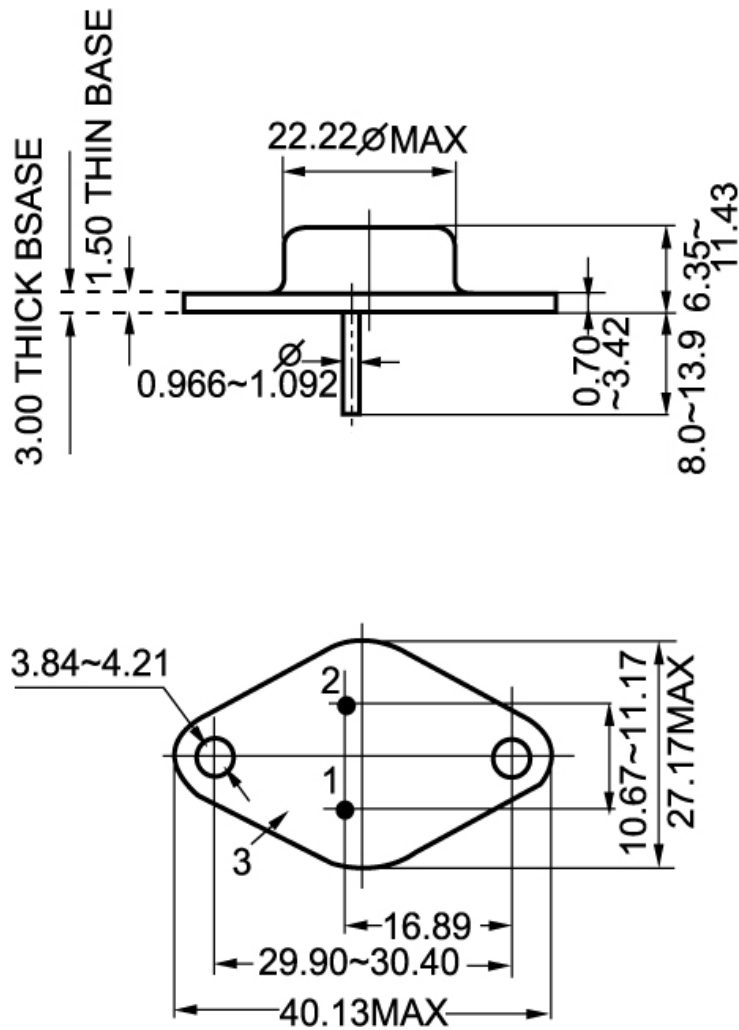


Fig.2 Outline dimensions